



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants:

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Title:

MANUFACTURING METHOD FOR A SEMICONDUCTOR SUBSTRATE COMPRISING AT LEAST A BURIED CAVITY AND DEVICES FORMED WITH THIS METHOD

Serial Number:

10/726,005

Filing Date:

December 1, 2003

Examiner/Unit:

Monica D. Harrison / 2812

Attorney Docket No.: 2110-91-3

CERTIFICATE OF MAILING OR TRANSMISSION

I hereby certify that this correspondence is being deposited in the United States Postal Service as First Class Mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on this 28th day of July, 2005.


Signature

RESPONSE TO RESTRICTION REQUIREMENT UNDER 37 CFR § 1.143

TO THE COMMISSIONER FOR PATENTS:

in response to the June 28, 2005 restriction requirement under 35 USC § 121, Applicants elect Group I (Claims 1-17 and 41-45) for prosecution with traverse.

According to MPEP § 803, if the Examiner can search and examine the application without serious burden, then he/she **MUST** examine the application on the merits even though it includes claims to independent or distinct inventions. As discussed below, because claims 1 – 45 recite related subject matter, the Examiner can perform a single search and examination that will cover all of the claims. Consequently, the Examiner can search and examine the application without serious burden, and, therefore, **MUST** examine all of the claims 1 – 45 together.

For example, claims 1 – 17 are directed to a SOI-type semiconductor substrate comprising at least a buried insulating cavity, and claims 18 – 28 are directed to a method for forming a semiconductor substrate such as that recited in claims 1 – 17. In fact, the body of independent claim 1 is virtually identical to the body of independent claim 18. Similarly, method claims 29 – 40 are directed to a method for forming a cavity in a substrate, and claims 41 and 45 are respectively directed to a substrate having a cavity and to a dielectric layer having a remnant of a cavity. Therefore, during her search for the elected Group I device claims 1 – 17 and 41-45, the references that the Examiner finds will include both semiconductor structures having cavities and methods for forming these structures. Consequently, a single search will find references for both the elected Group I structure claims 1 – 17 and 41 – 45 and the unelected Group II method claims 18-40.

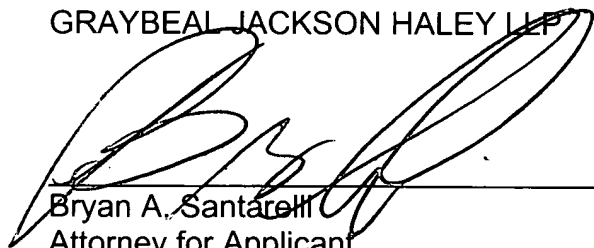
In the event additional fees are due as a result of this amendment, payment for those fees has been enclosed in the form of a check. Should further payment be required to cover such fees you are hereby authorized to charge such payment to Deposit Account No. 07-1897.

If after considering this response the Examiner continues to believe that the restriction is proper, she is respectfully requested to contact the Applicants' attorney, Bryan Santarelli, at (425) 455-5575, to schedule a telephone interview.

DATED this 28th day of July, 2005.

Respectfully submitted,

GRAYBEAL JACKSON HALEY LLP

A large, stylized handwritten signature in black ink, likely belonging to Bryan A. Santarelli, is written over a horizontal line.

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